



Description

The IPD30N06S2L-23 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 50A$

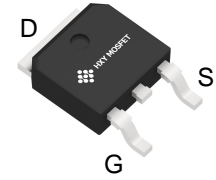
$R_{DS(ON)} < 17m\Omega$ @ $V_{GS}=10V$

Application

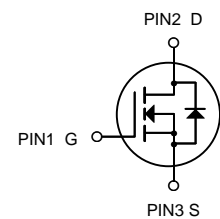
Battery protection

Load switch

Uninterruptible power supply



TO-252-2L
(DPAK)



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD30N06S2L-23	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	38	A
I_{DM}	Pulsed Drain Current ²	180	A
EAS	Single Pulse Avalanche Energy ³	280	mJ
I_{AS}	Avalanche Current	28	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	87.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ\text{C/W}$



Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=30A$	-	13	17	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=30A$	30	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	2498	-	PF
Output Capacitance	C_{oss}		-	185	-	PF
Reverse Transfer Capacitance	C_{rss}		-	80	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=1\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	12	-	nS
Turn-on Rise Time	t_r		-	5.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	38	-	nS
Turn-Off Fall Time	t_f		-	27	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=30A,$ $V_{GS}=10V$	-	36	-	nC
Gate-Source Charge	Q_{gs}		-	9.9	-	nC
Gate-Drain Charge	Q_{gd}		-	6.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	58	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 30A$ $di/dt = 100A/\mu s$ (Note3)	-	35		nS
Reverse Recovery Charge	Q_{rr}		-	47		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$



Typical Electrical and Thermal Characteristics (Curves)

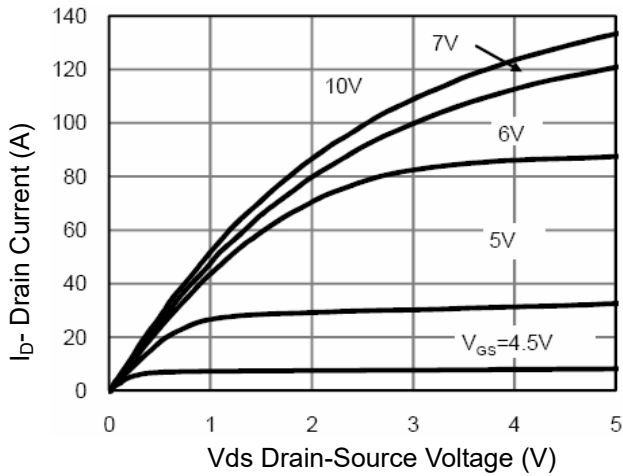


Figure 1 Output Characteristics

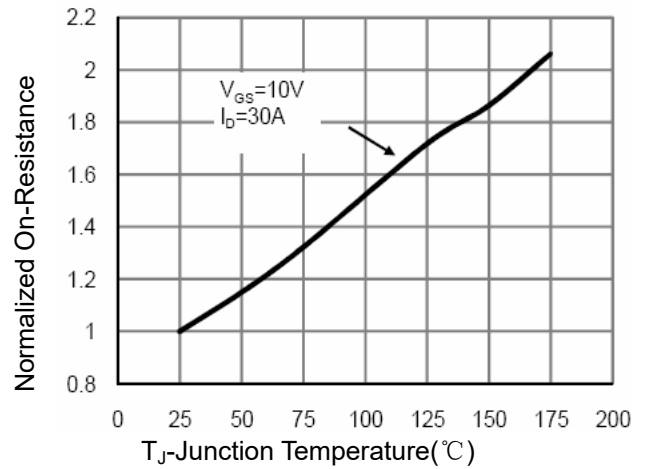


Figure 4 R_{dson} -Junction Temperature

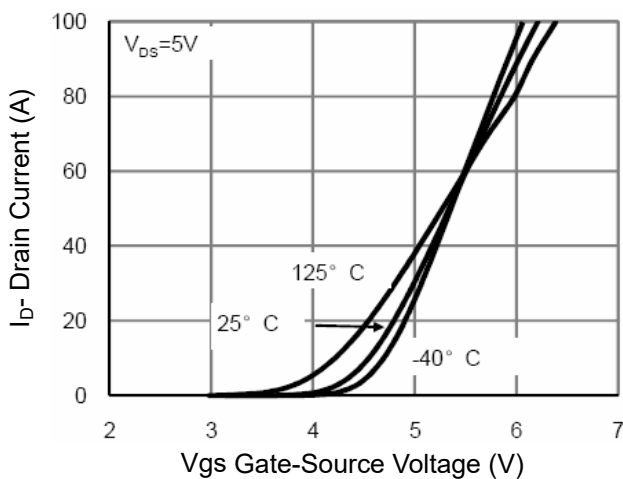


Figure 2 Transfer Characteristics

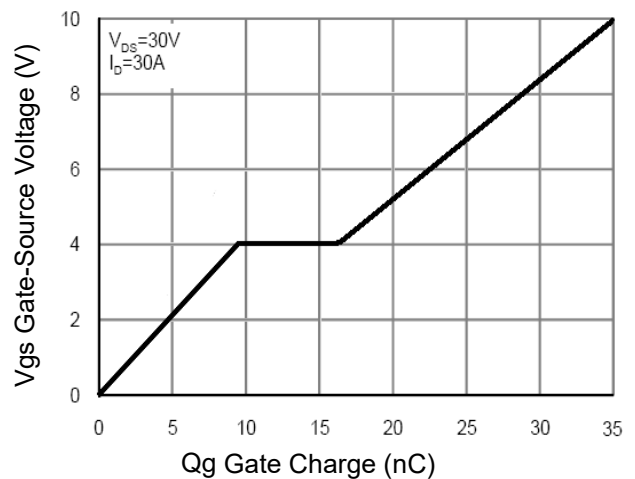


Figure 5 Gate Charge

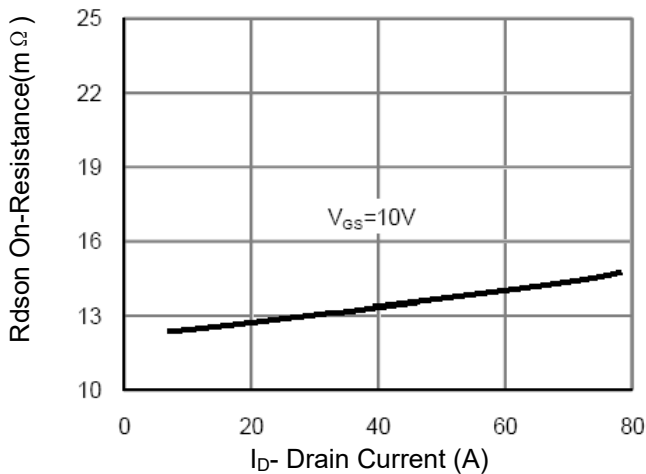


Figure 3 R_{dson} - Drain Current

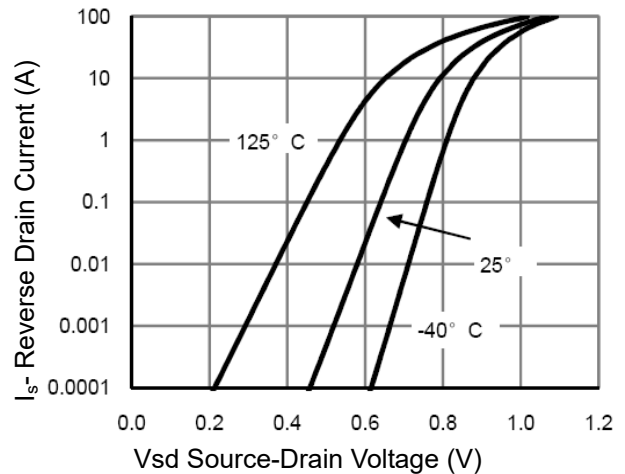


Figure 6 Source- Drain Diode Forward

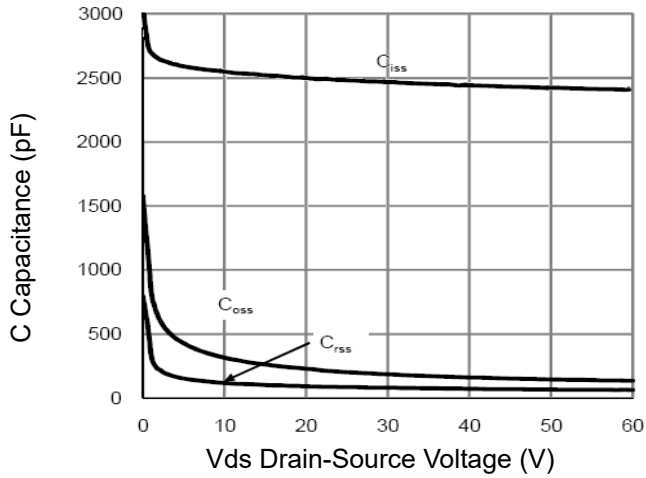


Figure 7 Capacitance vs Vds

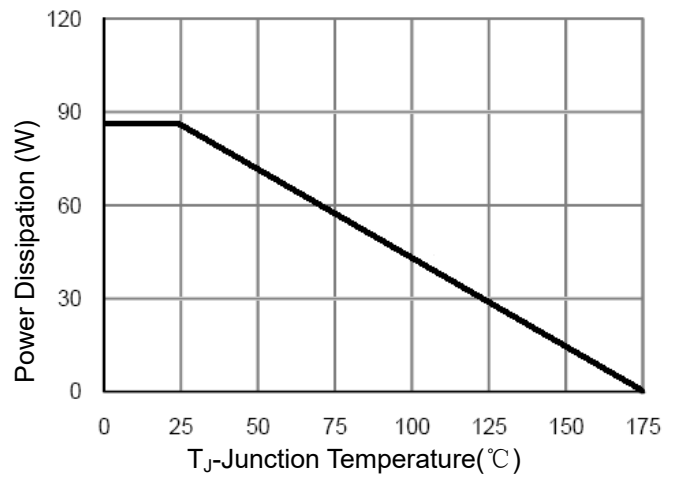


Figure 9 Power De-rating

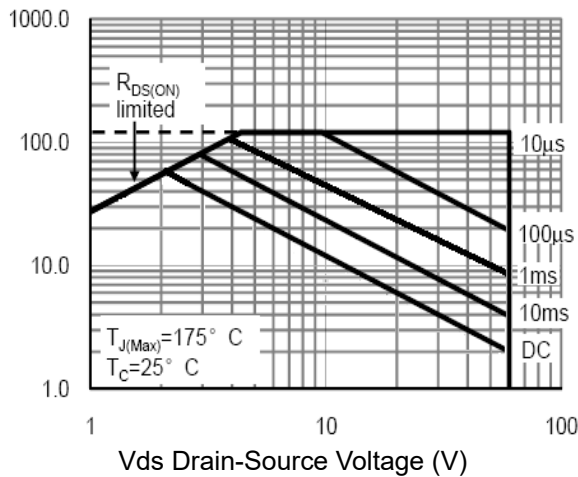


Figure 8 Safe Operation Area

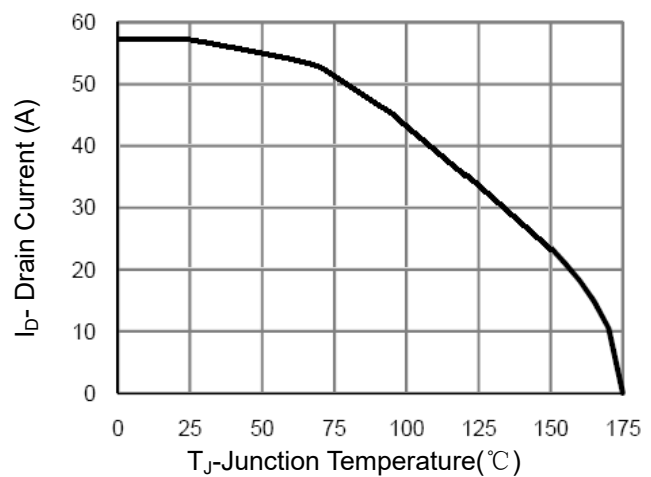
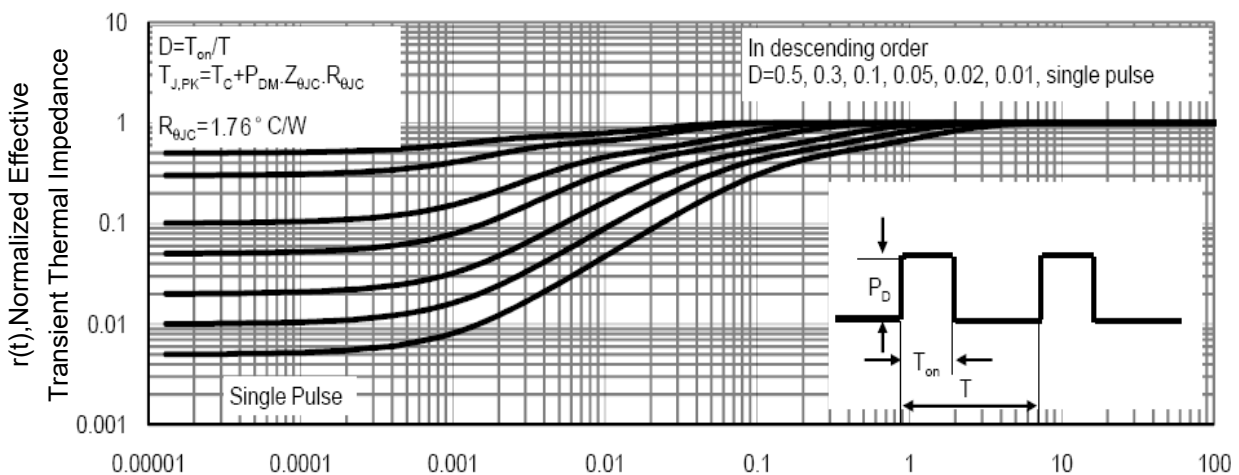
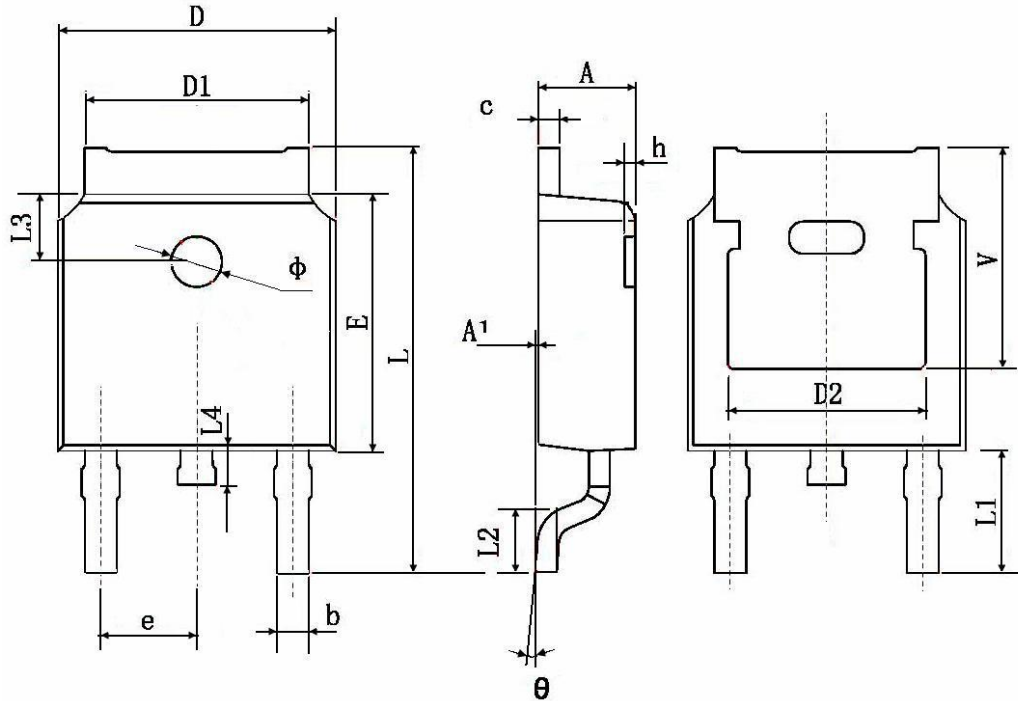


Figure 10 ID Current- Junction Temperature





TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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